

WHAT IS CLAIMED IS:

1. An organic EL panel having a plurality of organic EL elements arranged in a matrix, comprising:

5 a drive transistor provided to each of the plurality of organic EL elements, for controlling a drive current to be supplied to a corresponding organic EL element; and

a peripheral transistor provided near the periphery of a display area where the plurality of organic EL elements are arranged,
10 for outputting a signal for controlling the drive transistor, wherein

a gate length of the drive transistor is set longer than a gate length of the peripheral transistor.

15 2. The organic EL panel according to claim 1, wherein the gate length of the peripheral transistor is set to a value between 1 and 10 μm .

3. The organic EL panel according to claim 1, wherein
20 the gate length of the drive transistor is set to a value between 10 and 100 μm .

4. The organic EL panel according to claim 1, wherein
a gate width of the drive transistor and a gate width of the
25 peripheral transistor are set to the same value.

5. An organic EL panel having a plurality of organic EL elements

arranged in a matrix, comprising:

a drive transistor provided to each of the plurality of organic EL elements, for controlling a drive current to be supplied to a corresponding organic EL element; and

5 a peripheral transistor provided near the periphery of a display area where the plurality of organic EL elements are arranged, for outputting a signal for controlling the drive transistor, wherein

(a gate length L)/(a gate width W) of the drive transistor
10 is set larger than (a gate length L)/(a gate width W) of the peripheral transistor.

6. The organic EL panel according to claim 5, wherein the gate length of the peripheral transistor is set to a value
15 between 1 and 10 μm .

7. The organic EL panel according to claim 5, wherein the gate length of the drive transistor is set to a value between 10 and 100 μm .

20 8. The organic EL panel according to claim 5, wherein the gate width of the peripheral transistor is set to a value between 5 and 500 μm .

25 9. The organic EL panel according to claim 5, wherein the gate width of the drive transistor is set to a value between 5 and 10 μm .